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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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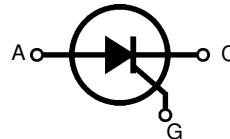
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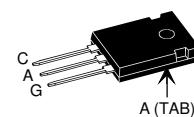
# Phase Control Thyristor

**V<sub>RRM</sub> = 800-1600 V**  
**I<sub>T(RMS)</sub> = 75 A**  
**I<sub>T(AV)M</sub> = 48 A**

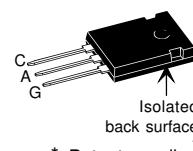
V <sub>RSM</sub>	V <sub>RRM</sub>	Type
V <sub>DSM</sub>	V <sub>DRM</sub>	
V	V	
900	800	CS 45-08io1
1300	1200	CS 45-12io1
1700	1600	CS 45-16io1 CS 45-16io1R



**TO-247 AD**  
Version io1



**ISOPLUS 247™**  
Version io1R



\* Patent pending

C = Cathode, A = Anode, G = Gate

Symbol	Conditions	Maximum Ratings		
I <sub>T(RMS)</sub>	T <sub>VJ</sub> = T <sub>VJM</sub>	75	A	
I <sub>T(AV)M</sub>	T <sub>C</sub> = 75°C; 180° sine	48	A	
I <sub>TSM</sub>	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	520 560	A A
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	460 500	A A
I <sup>2</sup> t	T <sub>VJ</sub> = 45°C V <sub>R</sub> = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1350 1300	A <sup>2</sup> s A <sup>2</sup> s
	T <sub>VJ</sub> = T <sub>VJM</sub> V <sub>R</sub> = 0 V	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1050 1030	A <sup>2</sup> s A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> f = 50 Hz, t <sub>p</sub> = 200 µs V <sub>D</sub> = 2/3 V <sub>DRM</sub> I <sub>G</sub> = 0.3 A di <sub>G</sub> /dt = 0.3 A/µs	repetitive, I <sub>T</sub> = 40 A non repetitive, I <sub>T</sub> = I <sub>T(AV)M</sub>	150 500	A/µs A/µs
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> ; R <sub>GR</sub> = ∞; method 1 (linear voltage rise)	V <sub>DR</sub> = 2/3 V <sub>DRM</sub>	1000	V/µs
P <sub>GM</sub>	T <sub>VJ</sub> = T <sub>VJM</sub> I <sub>T</sub> = I <sub>T(AV)M</sub>	t <sub>p</sub> = 30 µs t <sub>p</sub> = 300 µs	10 5 0.5	W W W
P <sub>G(AV)</sub>				
V <sub>RGM</sub>			10	V
T <sub>VJ</sub>			-40...+140	°C
T <sub>VJM</sub>			140	°C
T <sub>stg</sub>			-40...+125	°C
M <sub>d</sub>	Version io1: mounting torque M3		0.8...1.2	Nm
F <sub>c</sub>	Version io1R: mounting force with clip		20...120	N
V <sub>ISOL</sub> *	50/60 Hz, RMS, t = 1 minute, leads-to-tab		2500	V~
Weight			6	g

\* Version io1R only

Data according to IEC 60747  
IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Conditions	Characteristic Values		
$I_R, I_D$	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	$\leq$	5	mA
$V_T$	$I_T = 80 \text{ A}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.64	V
$V_{TO}$	For power-loss calculations only ( $T_{VJ} = 125^\circ\text{C}$ )	0.85	V	
$r_T$		11	mΩ	
$V_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	1.5	V
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	1.6	V
$I_{GT}$	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	$\leq$	100	mA
	$T_{VJ} = -40^\circ\text{C}$	$\leq$	200	mA
$V_{GD}$	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	$\leq$	0.2	V
$I_{GD}$		$\leq$	10	mA
$I_L$	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}; dI_G/dt = 0.3 \text{ A}/\mu\text{s}$	$\leq$	150	mA
$I_H$	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	$\leq$	100	mA
$t_{gd}$	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 \text{ A}; dI_G/dt = 0.3 \text{ A}/\mu\text{s}$	$\leq$	2	μs
$R_{thJC}$	DC current		0.62	K/W
$R_{thJH}$	DC current		0.82	K/W
$a$	Max. acceleration, 50 Hz		50	m/s <sup>2</sup>

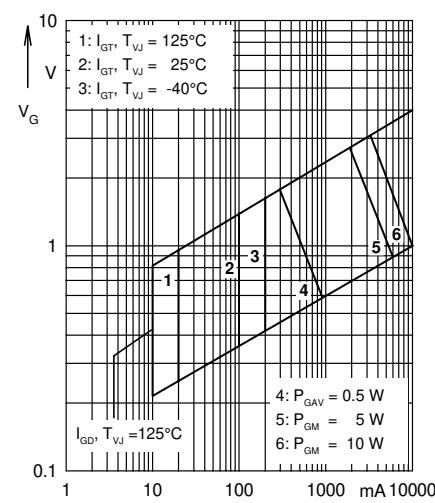
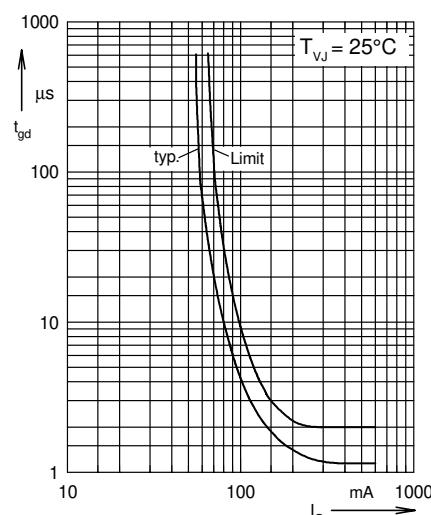
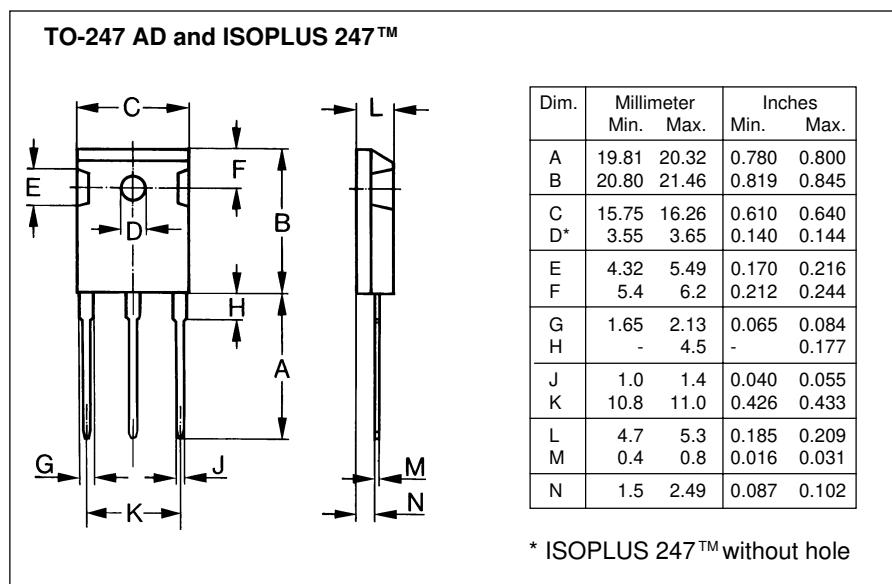


Fig. 1 Gate trigger range

Fig. 2 Gate controlled delay time  $t_{gd}$ 

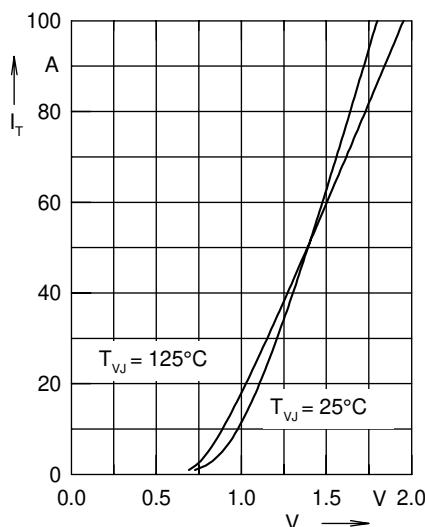


Fig. 3 Forward characteristics

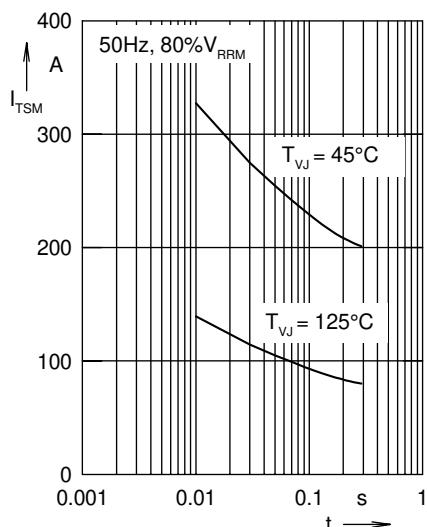


Fig. 4 Surge overload current  
 $I_{TSM}$ : crest value, t: duration

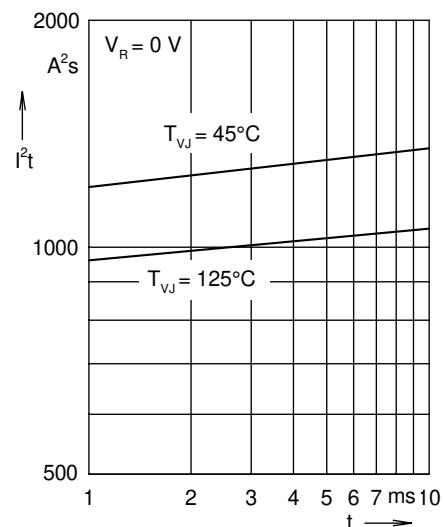


Fig. 5  $I^2t$  versus time (1-10 ms)

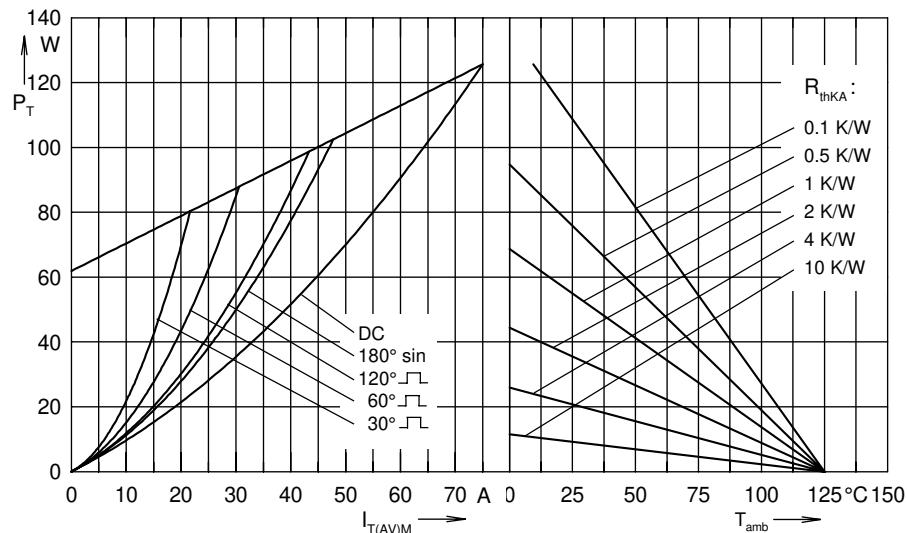


Fig. 6 Power dissipation versus forward current and ambient temperature

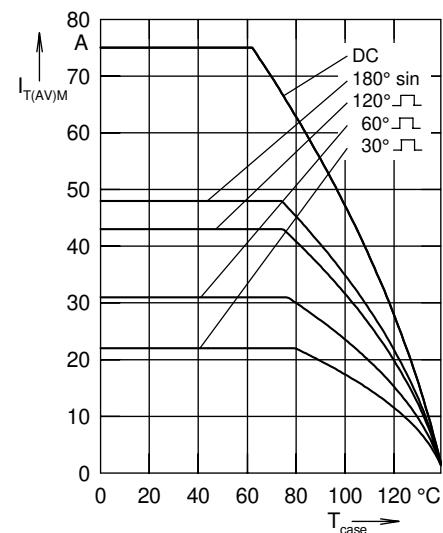


Fig. 7 Max. forward current at case temperature

$R_{thJC}$  for various conduction angles d:

d	$R_{thJC}$ (K/W)
DC	0.62
180°	0.71
120°	0.748
60°	0.793
30°	0.817

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.206	0.013
2	0.362	0.118
3	0.052	1.488

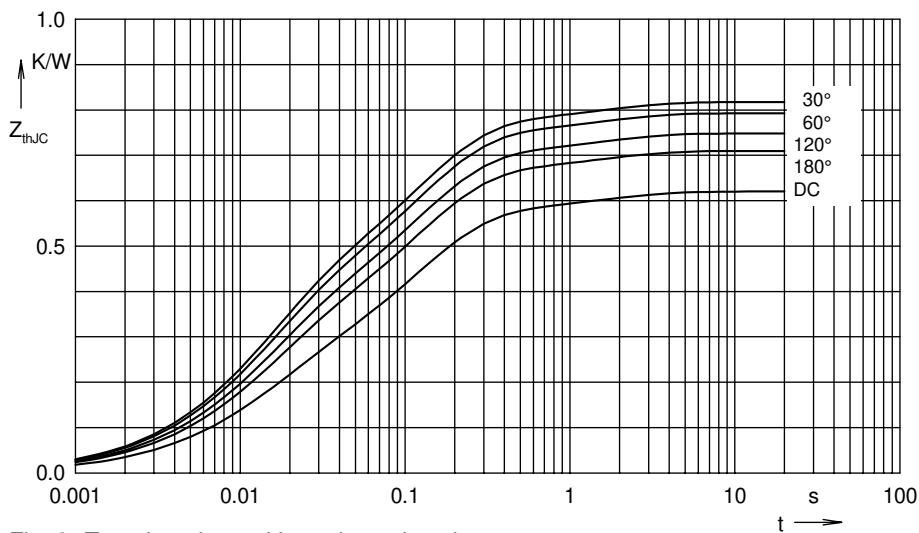


Fig. 8 Transient thermal impedance junction to case